

MMIC-Compatible 55 mW InP and GaAs 30 - 40 GHz Field Controlled TE-Oscillators

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55 mW 34 GHz InP, 56 mW 29 GHz GaAs and 39 mW 37 GHz GaAs lateral MMIC-compatible transferred electron oscillators with MESFET injection contacts have been fabricated exhibiting 2.9%, 5.3% and 4.9% efficiencies, respectively. CW power levels are somewhat lower (30 mW). The achieved power levels are the highest ever obtained with lateral TEOs and FET-oscillators.

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